TOSHIBA Photocoupler GaAs Ired & Photo-Triac

TLP360J

Triac Drivers Programmable Controllers AC-Output Modules Solid State Relays

The TOSHIBA TLP360J consists of a photo-triac optically coupled to a gallium arsenide infrared-emitting diode in a four-lead plastic DIP package.

• Peak off-state voltage: 600 V (Min.) • Trigger LED current: 10 mA (Max.)

· On-state current: 100 mA (Max.) • Isolation voltage: 5000 Vrms (Max.)

· UL recognized: UL1577, file No. E67349

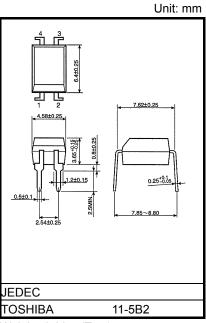
· Option (D4) type

TÜV approved: DIN EN60747-5-2

Certificate No. R50033433

Maximum operating insulation voltage : 890 Vpk Maximum permissible overvoltage : 8000 Vpk

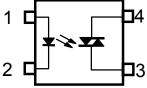
(Note) When an EN60747-5-2 approved type is needed, please designate "Option (D4)."



Weight: 0.26 g (Typ.)

· Construction mechanical rating

	7.62 mm pitch standard type	10.16 mm pitch TLPXXXF type		
Creepage distance Clearance	7.0 mm (min) 7.0 mm (min)	8.0 mm (min) 8.0 mm (min)		
Insulation thickness	0.4 mm (min)	0.4 mm (min)		



Pin Configuration (top view)

Trigger LED Current

Classi- fication*	Trigger LED	Marking of	
	$V_{T} = 6 V$	classification	
	Min.	Max.	Classification
(IFT7)	-	7	T7
Standard	1	10	T7, blank

^{*}Example: "(IFT7)"; "TLP360J(IFT7)"

(Note) When specifying the application type name for certification testing, be sure to use the standard product type name, e.g., TLP360J(IFT7): TLP360J.

1: Anode

2: Cathode

3: Terminal1

4: Terminal2

Absolute Maximum Ratings (Ta = 25°C)

Characteristic				Rating	Unit	
	Forward current			50	mA	
	Forward current derating (Ta ≥ 53°C)		ΔI _F /°C	-0.7	mA /°C	
LED	Peak forward current (100 µs pulse, 100 pps)		I _{FP}	1	Α	
	Reverse voltage		V _R	5	V	
	Junction temperature		Tj	125	°C	
	Off-state output terminal voltage		V_{DRM}	600	V	
	On-state RMS current	Ta = 25°C	IT(DMO)	100	mA	
_	On-state KWO current	Ta = 70°C	I _{T(RMS)}	50		
Detector	On-state current derating (Ta ≥ 25°C)	ΔI _T /°C	-1.1	mA /°C		
Ŏ	Peak on-state current (100 µs pulse, 120 pps)		I _{TP}	2	Α	
	Peak nonrepetitive surge current (Pw = 10 ms, DC =	10%)	I _{TSM}	1.2	Α	
	Junction temperature	Tj	115	°C		
Stor	rage temperature range	T _{stg}	-55~125	°C		
Оре	Operating temperature range			-40~100	°C	
Lea	Lead soldering temperature (10 s)			260	°C	
Isola	Isolation voltage (AC, 1 min., R.H.≤ 60%) (Note 1)			5000	Vrms	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pins 1 and 2 are shorted together and pins 3 and 4 are shorted together.

Recommended Operating Conditions

<u> </u>					
Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V _{AC}	_	_	240	V_{ac}
Forward current	lF	15	20	25	mA
Peak on-state current	I _{TP}	_	_	1	Α
Operating temperature	T _{opr}	-25	_	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	VF	I _F = 10 mA	1.0	1.15	1.3	V
LED	Reverse current	I _R	V _R = 5 V	_	_	10	μA
	Capacitance	C _T	V = 0, f = 1 MHz	_	30	_	pF
	Peak off-state current	I _{DRM}	V _{DRM} = 600 V	_	10	1000	nA
L	Peak on-state voltage	V _{TM}	I _{TM} = 100 mA	_	1.7	3.0	V
Detector	Holding current	lΗ	_	_	0.6	_	mA
Det	Critical rate of rise of off-state voltage	dv/dt	Vin = 240 Vrms , Ta = 85°C (Note 2)	_	500	_	V/µs
	Critical rate of rise of commutating voltage	dv/dt(c)	Vin = 60 Vrms , I _T = 15 mA (Note 2)		0.2		V/µs

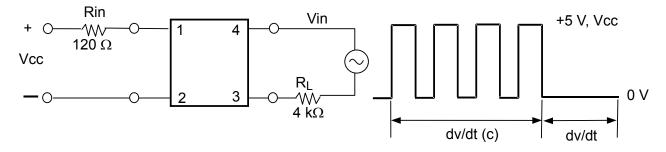
Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Trigger LED current	I _{FT}	V _T = 6 V	_	_	10	mA
Turn-on time	t _{ON}	V_D = 6 \rightarrow 4 V , R_L = 100 Ω I_F = Rated I_{FT} X1.5	l	30	100	μs

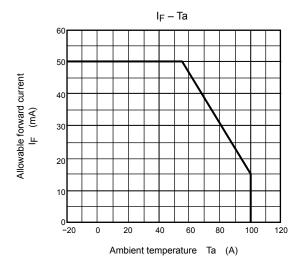
Isolation Characteristics (Ta = 25°C)

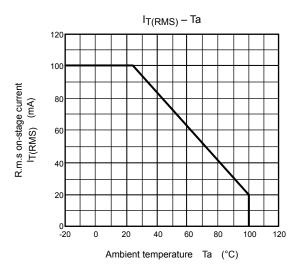
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance (input to output)	Cs	V _S = 0 , f = 1 MHz	_	0.8	_	pF
Isolation resistance	R _S	V _S = 500 V, R.H. ≤ 60%	1×10 ¹²	10 ¹⁴	_	Ω
Isolation voltage	BV_S	AC, 1 minute	5000	_	_	Vrms
		AC, 1 second, in oil	_	10000	_	VIIIIS
		DC, 1 minute, in oil	_	10000	1	Vdc

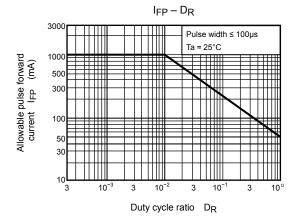
(Note 2): dv/dt test circuit

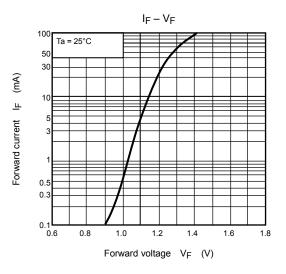


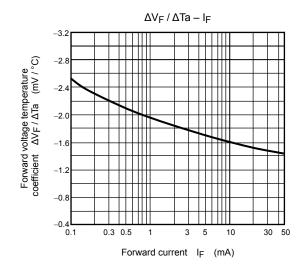
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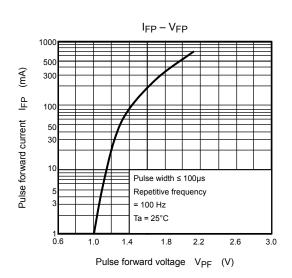






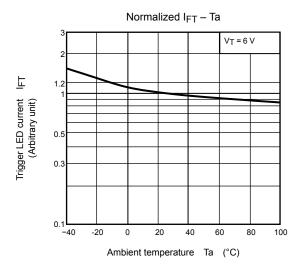


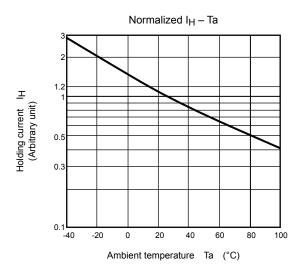


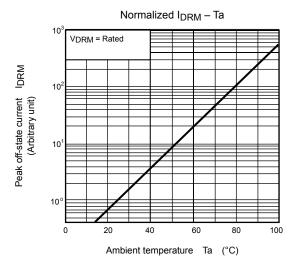


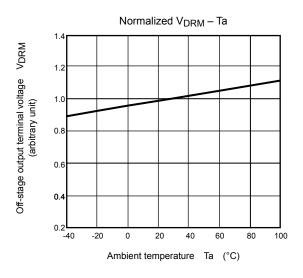
^{*:} The above graphs show typical characteristics.

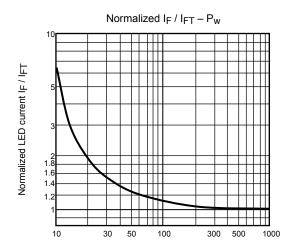
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*: The above graphs show typical characteristics.

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20070701-EN

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